

INDUCTORS

Inductance is ubiquitous:

Ampere's Law: $\nabla \times \bar{H} = \bar{J} + \partial \bar{D} / \partial t$

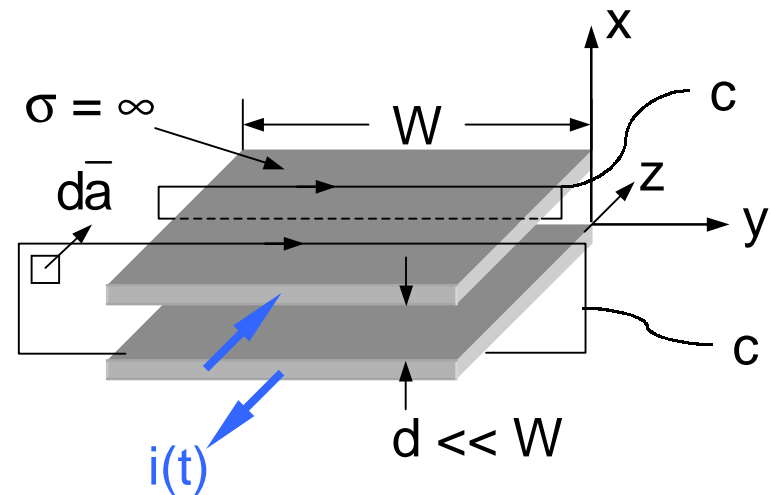
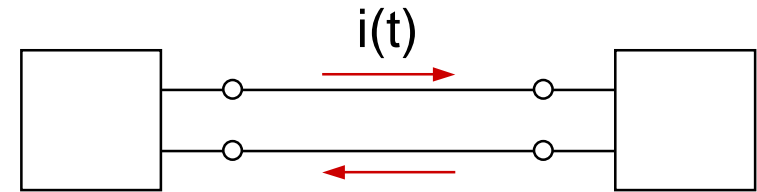
Let $\partial / \partial t \cong 0$

Example—printed circuit:

$$\oint_C \bar{H} \cdot d\bar{s} = \int_A \bar{J} \cdot d\bar{a}$$

= 0 around both wires

= $i(t)$ around the top wire



Magnetic Field H:

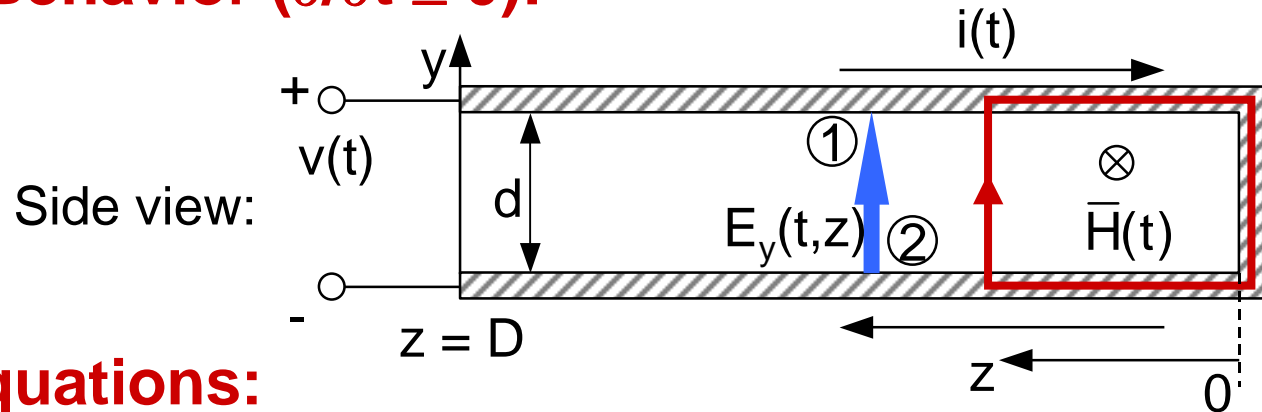
Outside: $\bar{H} \cong 0$

Inside: $\bar{H} \cong -\hat{y}i/W$

(since $d \ll W$ we ignore fringing fields)

INDUCTANCE

Quasistatic Behavior ($\partial/\partial t \cong 0$):



Maxwell's Equations:

Faraday's Law:

$$\nabla \times \bar{\mathbf{E}} = -\partial \bar{\mathbf{B}} / \partial t$$

$$\Rightarrow \int_C \bar{\mathbf{E}} \cdot d\bar{\mathbf{s}} = -\frac{d}{dt} \int_A \mu \bar{\mathbf{H}} \cdot d\bar{\mathbf{a}}$$

$$E_y(t, z) d = -(\mu z d / W) di(t) / dt \text{ [recall } H = i / W \text{]}$$

Therefore when $z = D$: $v(t) = \int_1^2 \bar{\mathbf{E}} \cdot d\bar{\mathbf{s}} = -E_y d = (\mu D d / W) (di(t) / dt)$

Note: $Dd =$ cross-sectional area A

$$v(t) = L di(t) / dt \text{ where } L = \mu A / W \text{ Henries}$$

Note: Kirchoff's voltage law not obeyed here; $E_y = f(z)$

SOLENOIDAL INDUCTORS

N-Turn Solenoidal Inductor:

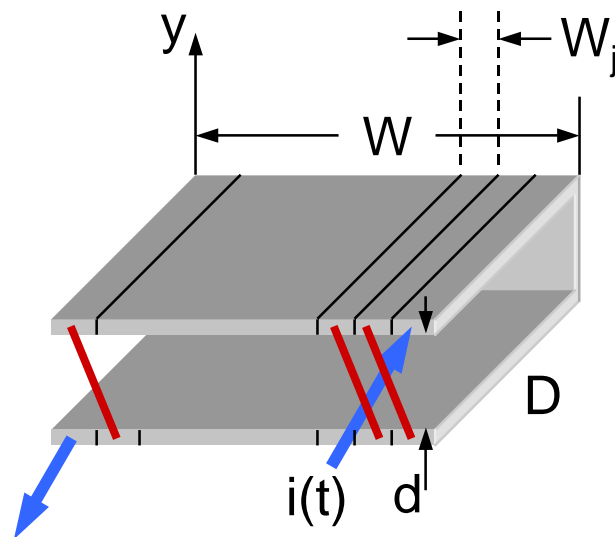
$$v(t) = \int_1^2 \bar{\mathbf{E}} \cdot d\bar{\mathbf{s}} = -E_y d = (\mu D d / W) (di(t) / dt)$$

$$v_j(t) = (\mu D d / W_j) (di(t) / dt) \text{ for } j^{\text{th}} \text{ turn}$$

$$\text{But: } W = N W_j$$

$$v(t) = N v_j(t)$$

$$\text{Therefore: } v(t) = (N^2 \mu D d / W) (di(t) / dt) ; D d = A$$



Inductance of N-Turn Solenoid:

$$L = N^2 \mu A / W \text{ Henries}$$

Magnetic Energy Storage:

$$w_m = \mu |\bar{\mathbf{H}}(t)|^2 / 2 \quad [\text{J m}^{-3}]$$

$$w_m = \mu D d W |\bar{\mathbf{H}}(t)|^2 / 2 = \mu A W (N i / W)^2 / 2 \quad [\text{J}] \quad [\text{recall } H = N i / W]$$

Therefore:

$$w_m = L i^2(t) / 2 \quad [\text{J}]$$

RESISTIVE INDUCTORS

Single-Turn Inductor:

Conductance of slab of cross-sectional area S : σS [Siemens m]

Resistance of slab of length D : $D/\sigma S$ [ohms]

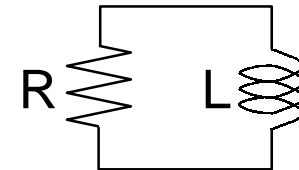
Resistance of a single-turn inductor: $2(D + d)/\sigma S$ [ohms] ($S = \delta W$)

Resistance of an N -turn inductor: $2N(D + d)/\sigma(S/N) = 2N^2(D + d)/\sigma S$

L/R Time Constant of Solenoidal Inductor:

$$\tau = L/R \text{ seconds}$$

$$\left(\text{e.g. } i(t) = i_0 e^{-t/\tau} \right)$$

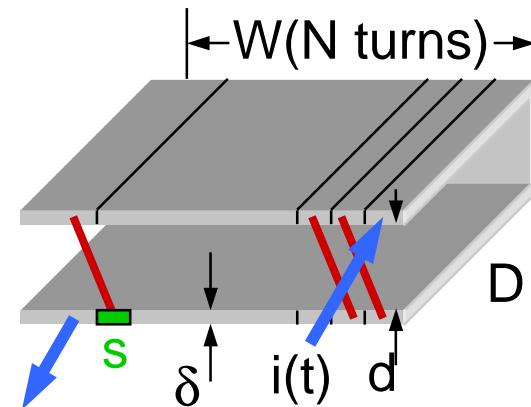


$$= (N^2 \mu A / W) / (2N^2 (D + d) / \sigma S) \cong \mu d \delta \sigma / 2N$$

where $D \gg d$, $S = \delta W$, $A = Dd$

For finite size and mass, τ is limited

Want $d \rightarrow D$, $\delta \rightarrow d/3$, $N \rightarrow 1$, $d \rightarrow W$



TRANSFORMERS

Air-Wound Solenoidal Transformers:

$$\oint_C \vec{E} \cdot d\vec{s} = -\frac{d}{dt} \int_A \mu \vec{H} \cdot d\vec{a}$$

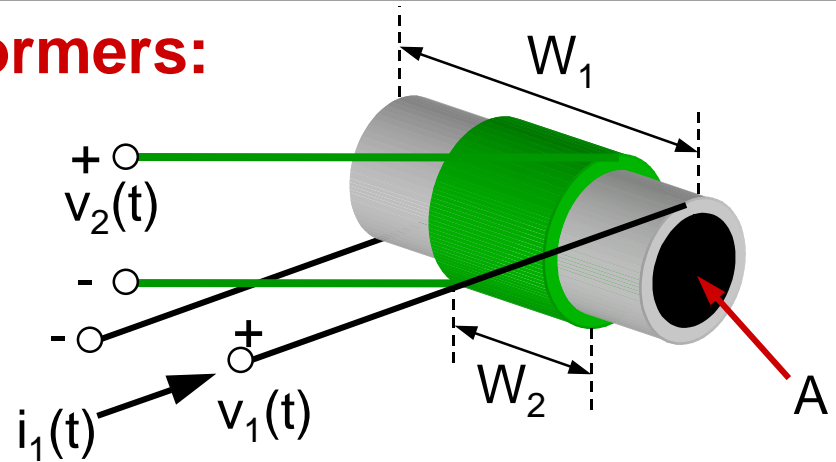
Say $A_1 = A_2$, $W_1 = W_2$ here
 N_i = number of turns in coil i

Therefore:

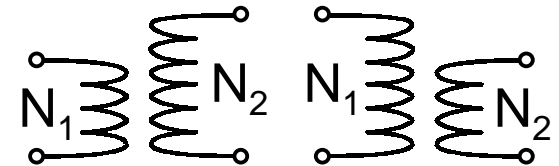
The voltage induced in one turn of coil 2 is the same as induced in one turn of coil 1,

And the total voltage induced in coil 2 is N_2/N_1 times the total voltage induced in coil 1, regardless of whether it is generated by i_1 or i_2 .

N_2/N_1 is called the transformer turns ratio



Step-up and Step-down Transformers:



Step-up or step-down the output voltage, correspondingly.
 The flux coupling between the two coils may be imperfect
 and the output voltage is correspondingly reduced

[flux $\Lambda = \mu HA$, and linked flux = $N\mu HA$].

IRON-CORE TRANSFORMERS (1)

Boundary Conditions:

$H_{//}$ and \bar{B}_{\perp} are continuous across the boundary

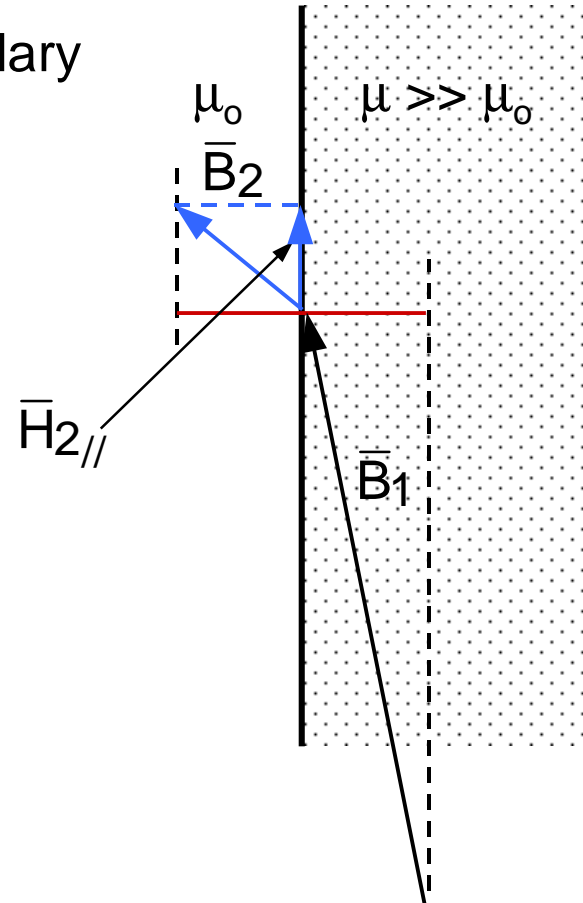
$$(\nabla \times \bar{H} = \bar{J} + \partial \bar{D} / \partial t; \nabla \cdot \bar{B} = 0)$$

$$\bar{H}_{//} \text{ and } \bar{B} = \mu \bar{H}$$

μ / μ_0 can be as large as 10^6 .

Since $\mu \gg \mu_0$, \bar{B}_1 is essentially parallel to the interface, and trapped within the high permeability medium.

The magnetic flux \bar{B} is "trapped" inside.

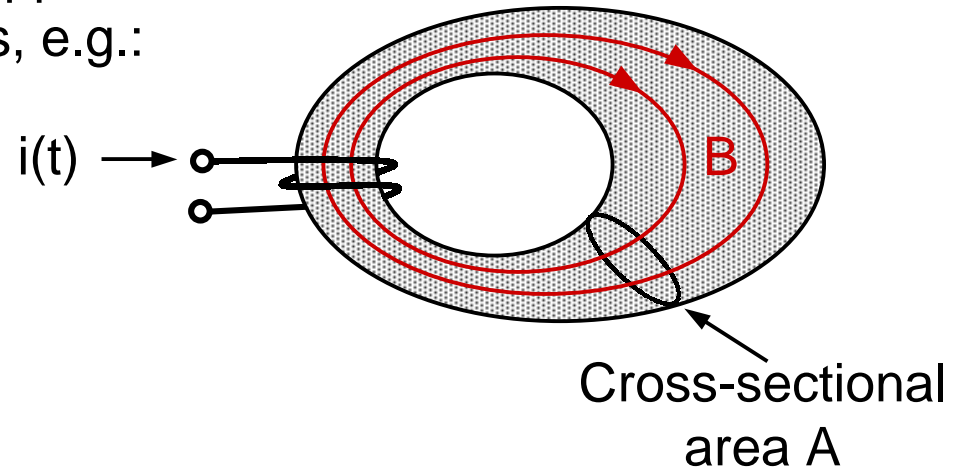


IRON-CORE TRANSFORMERS (2)

Flux trapping inside high permeability materials:

The magnetic flux density \bar{B} is trapped inside high-permeability materials, e.g.:

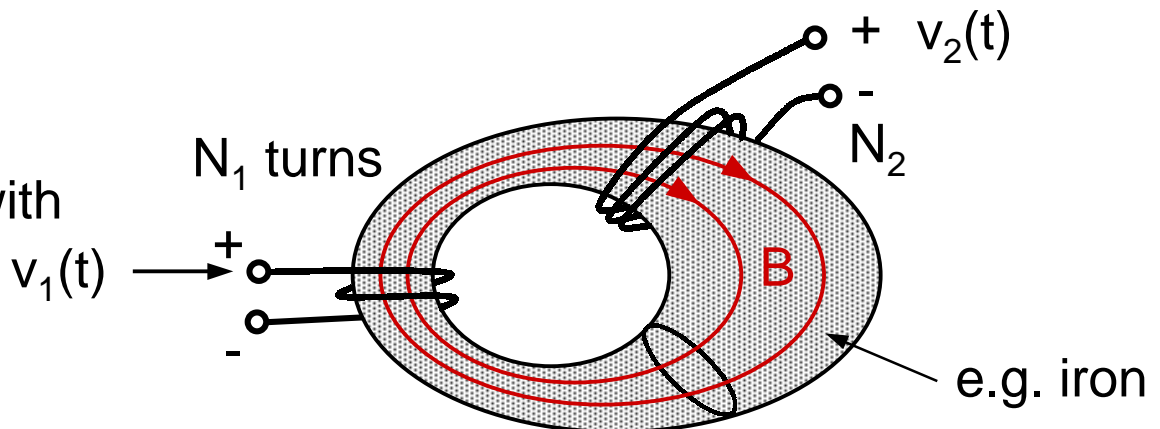
$$\text{Flux } \Lambda = \int_A \bar{B} \cdot d\bar{a} \cong \text{constant}$$



Transformer Output:

$$v_2(t) = (N_2/N_1)v_1(t)$$

The flux is highly linked with little leakage

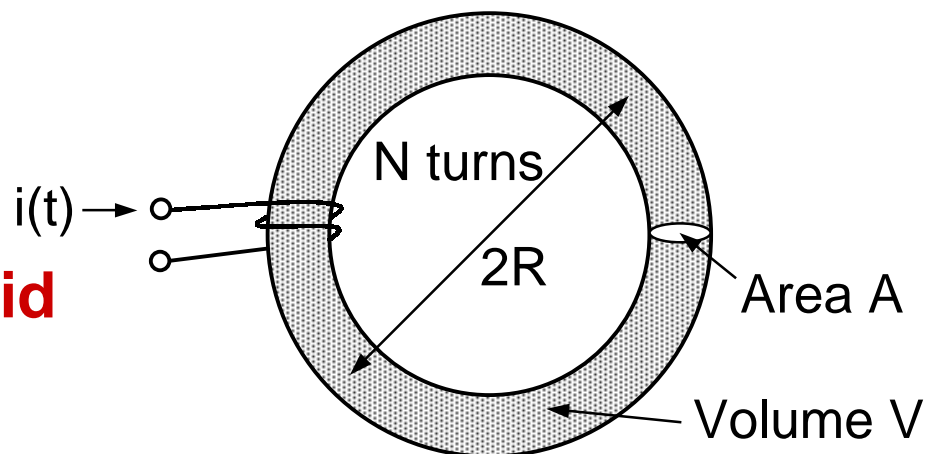


INDUCTANCE OF IRON TOROID (1)

Inductance L of N turns around toroid ($N_2 = 0$):

Recall: $w_m = Li^2(t)/2 = \int_V W_m dv$ [J] = $\int_V (\mu |\bar{H}|^2 / 2) dv$

where $W_m = \mu |\bar{H}(t)|^2 / 2$ [Jm⁻³]



Example: Constant Area Toroid

Since:

$$L = \left(\mu \int_V |\bar{H}(t)|^2 dv \right) / i^2(t)$$

$$\nabla \times \bar{H} = \bar{J} + \frac{\partial \bar{D}}{\partial t} \Rightarrow \oint_C \bar{H} \cdot d\bar{s} \cong Ni(t)$$

$\cong 0$

Therefore:

$$2\pi R |\bar{H}| \cong Ni \quad (R \text{ varies slightly over } A)$$

$$L \cong \mu \int_V (N/2\pi R)^2 dv \cong \mu (N/2\pi R)^2 V \cong \mu N^2 A / 2\pi R \quad [\text{Henries}]$$

where $V \cong 2\pi RA$ [m³]

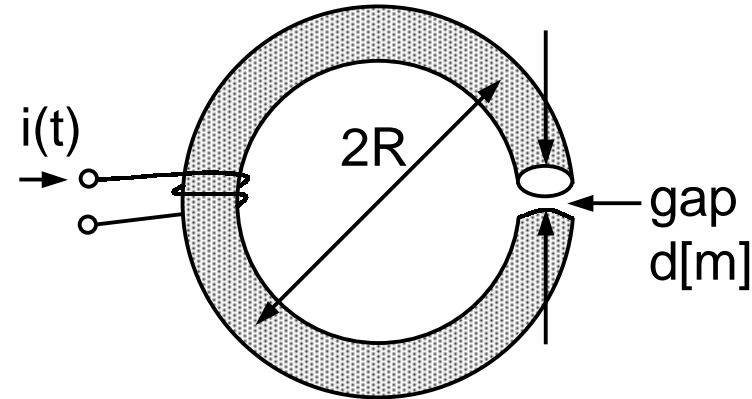
INDUCTANCE OF IRON TOROID (2)

Inductance L of a toroid with a gap:

Recall: $w_m = Li^2(t)/2 = \int_V W_m dv$ [J]

where $W_m = \mu |\bar{H}(t)|^2 / 2$ [Jm⁻³]

Therefore: $L = \left(\mu \int_V |\bar{H}(t)|^2 dv \right) / i^2(t)$, as before



Finding $|\bar{H}(t)|$:

Since: $\oint_C \bar{H} \cdot d\bar{s} \cong Ni(t)$

Therefore: $|\bar{H}_\mu| (2\pi R - d) + |\bar{H}_{\mu_0}| d \cong Ni(t)$

But $\nabla \cdot \bar{B} = 0$, so $\mu_0 H_0 = \mu H$ where we assume $\mu \gg \mu_0$

Therefore: Magnetic energy density in gap is $(\mu/\mu_0)^2$ greater than inside the torus, and dominates unless $(\mu/\mu_0)^2 \ll 2\pi R/d$

(we require $d \gtrsim 2\pi R (\mu_0/\mu)^2$)

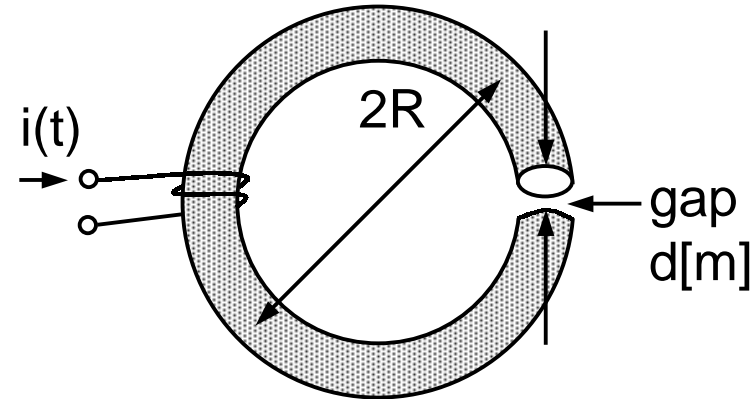
INDUCTANCE OF IRON TOROID (3)

Inductance L of a toroid with a gap:

Recall: $L = \left(\mu(t) \int_V |\bar{H}|^2 dv \right) / i^2$

$$|\bar{H}_\mu| (2\pi R - d) + |\bar{H}_{\mu_0}| d \cong Ni(t)$$

Where: $|\bar{H}_{\mu_0}| d \cong Ni(t)$ for a small gap with little fringing ($d \ll A^{0.5}$) and we neglect the energy storage inside the torus



Therefore: $L \cong \mu A d (N/d)^2$ or, for a small-gap torus:

$$L \cong \mu_0 A N^2 / d \quad \text{Henries}$$

provided that $d \gtrsim 2\pi R (\mu_0 / \mu)^2$